

SANYO	No. 1594B	2SC3460
NPN Triple Diffused Planar Silicon Transistor		
FOR SWITCHING REGULATORS		

Features

- . High breakdown voltage and high reliability.
- . Fast switching speed (t_f : 0.1 μ s typ.)
- . Wide ASO.
- . Adoption of MBIT process.

Absolute Maximum Ratings at Ta=25°C

		unit
Collector-to-Base Voltage	V_{CBO}	1100 V
Collector-to-Emitter Voltage	V_{CEO}	800 V
Emitter-to-Base Voltage	V_{EBO}	7 V
Collector Current	I_C	6 A
Peak Collector Current	i_{cp}	20 A
Base Current	I_B	3 A
Collector Dissipation	P_C	100 W
Junction Temperature	T_J	150 °C
Storage Temperature	T_{stg}	-55 to +150 °C

$T_C=25^\circ C$

$PW \leq 300\mu s, Duty\ Cycle \leq 10\%$

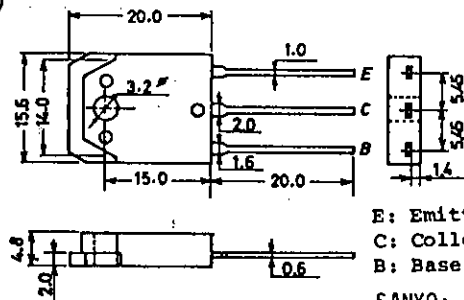
Electrical Characteristics at Ta=25°C

			min	typ	max	unit
Collector Cutoff Current	I_{CBO}	$V_{CB}=800V, I_E=0$			10	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB}=5V, I_C=0$			10	μA
DC Current Gain	$h_{FE(1)}$	$V_{CE}=5V, I_C=0.4A$	10*		40*	
	$h_{FE(2)}$	$V_{CE}=5V, I_C=2A$	8			
Gain-Bandwidth Product	f_T	$V_{CE}=10V, I_C=0.4A$		15		MHz
Output Capacitance	c_{ob}	$V_{CB}=10V, f=1MHz$		120		pF
C-E Saturation Voltage	$V_{CE(sat)}$	$I_C=3A, I_B=0.6A$			2.0	V
B-E Saturation Voltage	$V_{BE(sat)}$	$I_C=3A, I_B=0.6A$			1.5	V
C-B Breakdown Voltage	$V(BR)CBO$	$I_C=1mA, I_E=0$	1100			V
C-E Breakdown Voltage	$V(BR)CEO$	$I_C=5mA, R_{BE}=\infty$	800			V
E-B Breakdown Voltage	$V(BR)EBO$	$I_E=1mA, I_C=0$	7			V
C-E Sustain Voltage	$V_{CEX(sus)}$	$I_C=3A$	800			V
		$I_{B1}=-I_{B2}=0.6A,$				
		$L=1mH, clamped$				
Turn-On Time	t_{on}	$V_{CC}=400V,$ $5I_{B2}=-2.5I_{B2}=I_C=4A,$ $R_L=100\Omega$			0.5	μs
Storage Time	t_{stg}				3.0	μs
Fall Time	t_f				0.3	μs

*: The $h_{FE(1)}$ of the 2SC3460 is classified as follows. When specifying the $h_{FE(1)}$ rank, specify two ranks or more in principle.

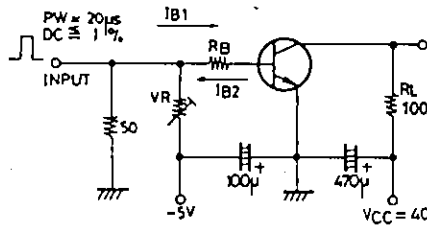
10	K	20	15	L	30	20	M	40
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Package Dimensions 2022
(unit:mm)

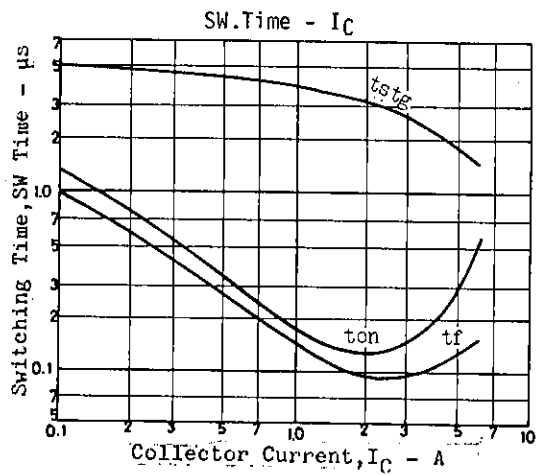
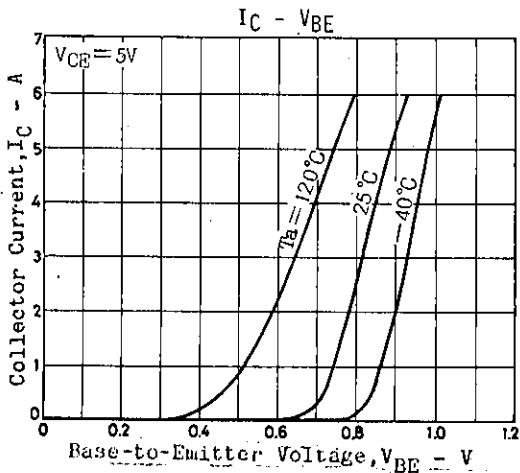
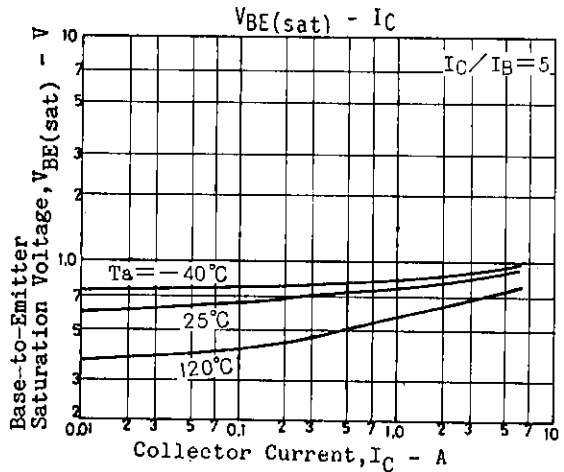
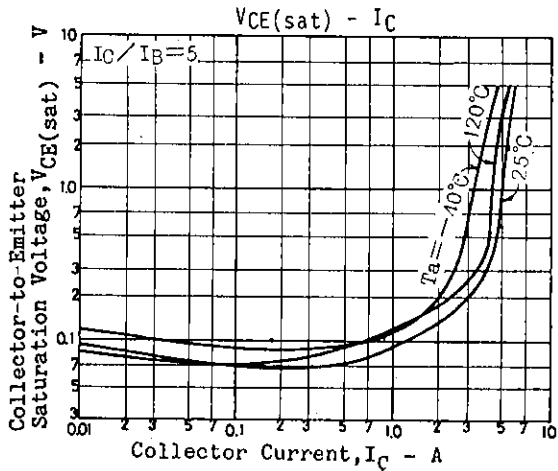
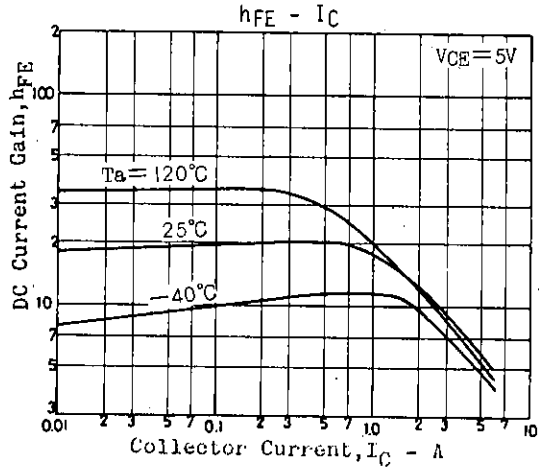
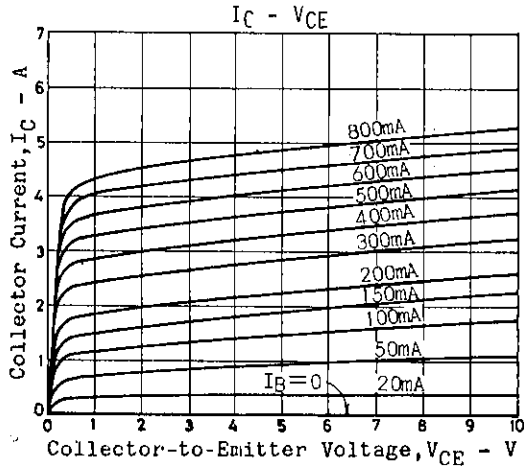


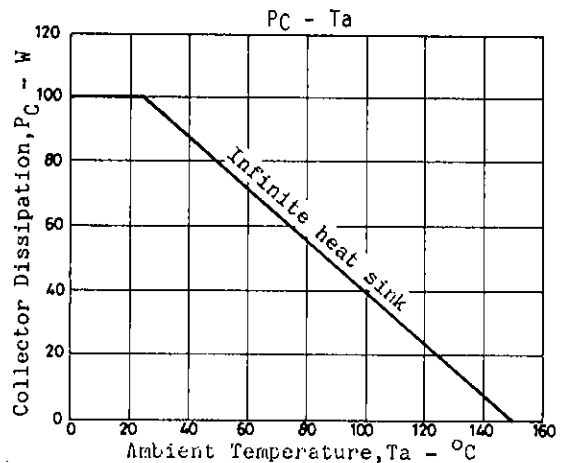
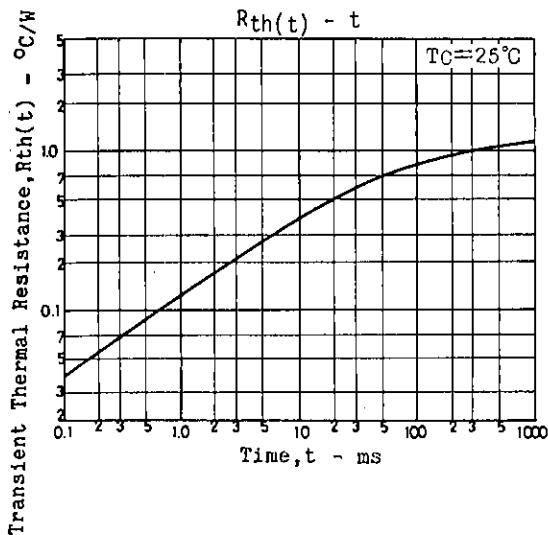
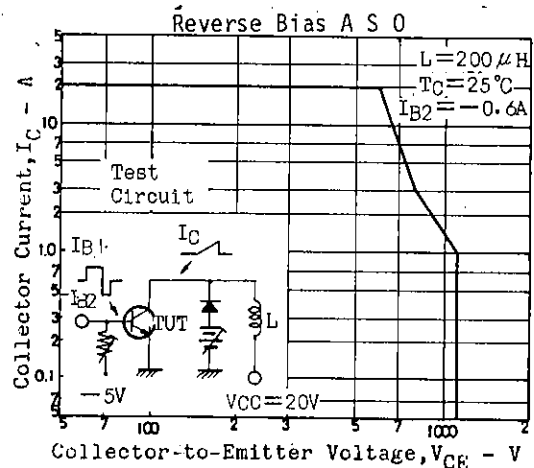
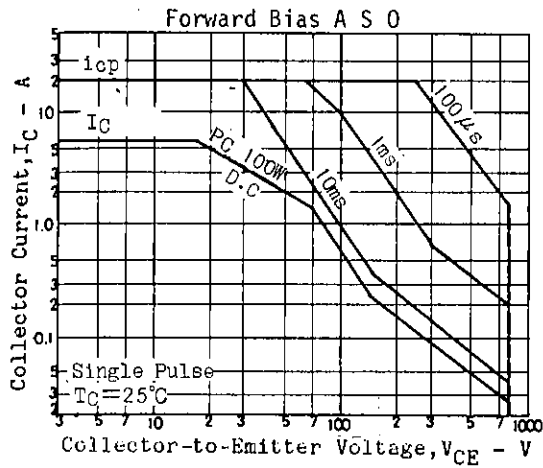
E: Emitter
C: Collector
B: Base
SANYO: TO3PB

Switching Time Test Circuit



Unit (Resistance : Ω, Capacitance : F)





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